Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

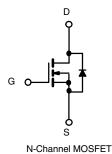
PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0017
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0020
I _D (A)	200
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE



ORDERING INFORMATION	
Package	PowerPAK 8x8L
Lead (Pb)-free and Halogen-free	SQJQ402E-T1-GE3

ABSOLUTE MAXIMUM RATIN	GS ($T_C = 25 ^{\circ}C$, unles	s otherwise noted	i)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	40		
Gate-Source Voltage	V_{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C ^a	1	200		
	T _C = 125 °C	I _D	127		
Continuous Source Current (Diode Conduc	ction)	I _S	200	Α	
Pulsed Drain Current ^b		I _{DM}	300		
Single Pulse Avalanche Current L = 0.1 mH		I _{AS}	85		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	361	mJ	
Maximum Power Dissipation	T _C = 25 °C	D	150	W	
	T _C = 125 °C	P_{D}	50		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) d, e			260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	R _{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$.
- c. When mounted on 1" square Pcb (Fr4 material).
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8x8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•			L	<u> </u>	L	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2	2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} =$	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	100	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0013	0.0017	
Drain Cauras On State Besistance		V _{GS} = 4.5 V	I _D = 10 A	-	0.0015	0.0020	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0026	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0031	
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 20 A	-	140	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			=.	10 760	13 500	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	=	1370	1800	рF
Reverse Transfer Capacitance	C _{rss}			-	650	850	
Total Gate Charge ^c	Q_g			=.	169	260	
Gate-Source Charge c	Q _{gs}	V _{GS} = 10 V	$V V_{DS} = 20 V, I_D = 40 A$		32	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	29	-	
Gate Resistance	R _g		f = 1 MHz	0.6	1.3	2.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	19	30	
Rise Time ^c	t _r	V _{DD} =	= 20 V, $R_L = 0.5 \Omega$	=	15	25	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 40 \text{ A},$	$V_{GEN} = \overline{10} \text{ V}, R_g = 1 \Omega$	-	69	110	ns
Fall Time ^c	t _f			-	11	20	
Source-Drain Diode Ratings and Cha	racteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	300	Α

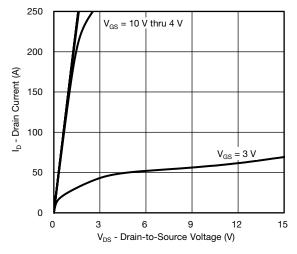
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

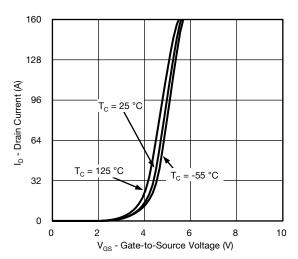
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



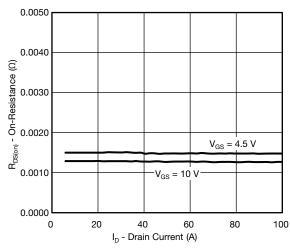
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



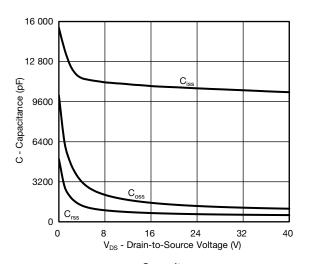
Output Characteristics



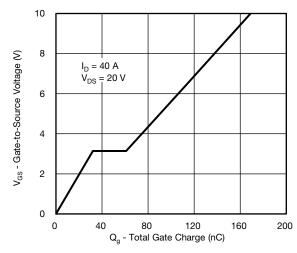
Transfer Characteristics



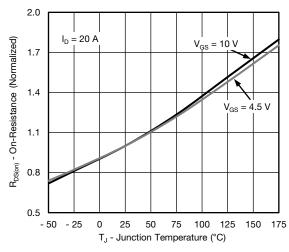
On-Resistance vs. Drain Current



Capacitance



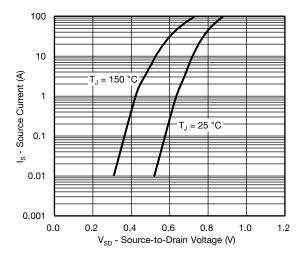
Gate Charge



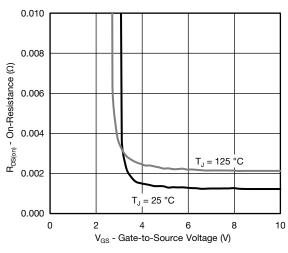
On-Resistance vs. Junction Temperature



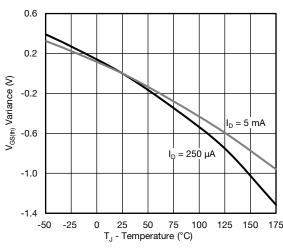
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



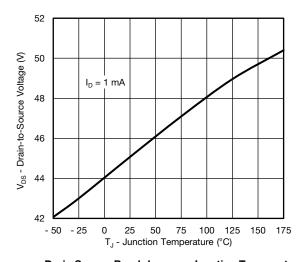
Source Drain Diode Forward Voltage



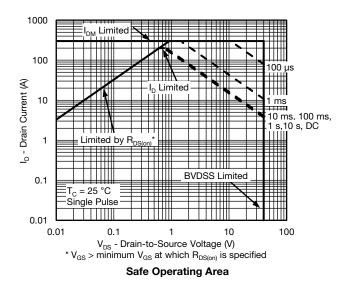
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

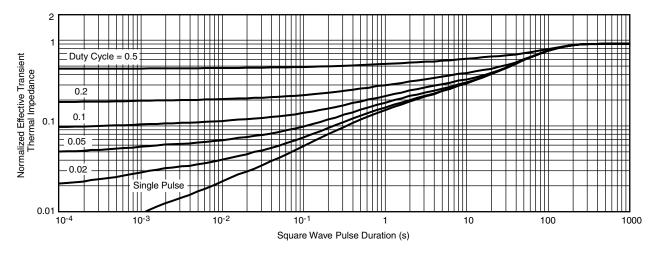


Drain Source Breakdown vs. Junction Temperature

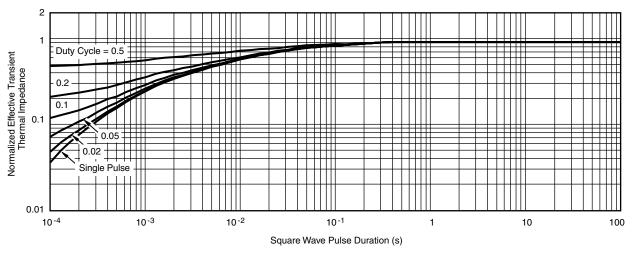




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



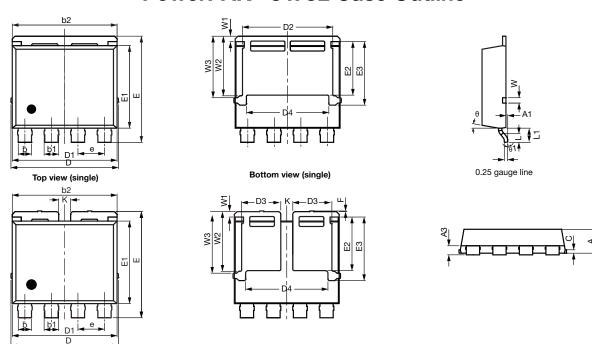
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62748.



Top view (dual)

PowerPAK® 8 x 8L Case Outline



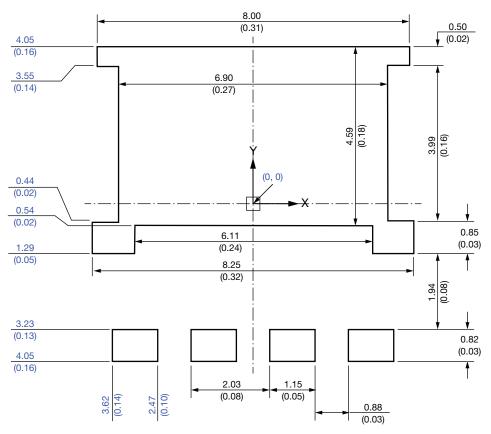
Bottom view (dual)

DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
е	1.95	2.00	2.05	0.077	0.079	0.081	
E	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
F	0.05	0.10	0.15	0.002	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
θ	6°	10°	14°	6°	10°	14°	
θ1	0°	3°	8°	0°	3°	8°	
θ1 -0891-Rev. A, G: 6026	ŭ	3°	8°	0°	3°		

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Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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